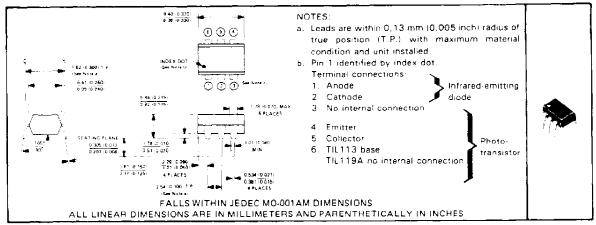
- Gallium Arsenide Diode Infrared Source Optically Coupled to a Silicon N-P-N Darlington-Connected Phototransistor
- High Direct-Current Transfer Ratio . . . 300% Minimum at 10 mA
- High-Voltage Electrical Isolation . . . 1500-Volt Rating
- Plastic Dual-In-Line Package
- Base Lead Provided on TIL 113 for Conventional Transistor Biasing
- No Base Lead Connection on TIL119A for High-EMI Environments
- Typical Applications Include Remote Terminal Isolation, SCR and Triac Triggers, Mechanical Relays, and Pulse Transformers

mechanical data

The package consists of a gallium arsenide infrared-emitting diode and an n-p-n silicon darlington-connected photo-transistor mounted on a 6-lead frame encapsulated within an electrically nonconductive plastic compound. The case will withstand soldering temperature with no deformation and device performance characteristics remain stable when operated in high-humidity conditions. Unit weight is approximately 0.52 grams.



absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Input-to-Output Voltage	٠V
Collector Base Voltage (TIL113)	V
Collector-Emitter Voltage (See Note 1)	V
Emitter-Collector Voltage	٧
Emitter Base Voltage (TIL113)	V
Input Diode Reverse Voltage	V
Input Diode Continuous Forward Current at (or below) 25°C Free Air Temperature (See Note 2)	
Continuous Power Dissipation at (or below) 25°C Free-Air Temperature.	
Infrared-Emitting Diode (See Note 3)	W
Phototransistor (See Note 4)	١VV
Total (Infrared-Emitting Diode plus Phototransistor, See Note 5)	١W
Storage Temperature Range	C
Lead Temperature 1,6 mm (1/16 Inch) from Case for 10 Seconds	

NOTES 1. This value applies when the base emitter diode is open circuited

- 2. Derate linearly to 100°C free air temperature at the rate of 1.33 mA. C
- Denote linearly to 100 C free air temperature at the rate of 2 mW/l C.
 Denote linearly to 100° C free air temperature at the rate of 2 mW/l C.
- 4. Denote linearly to 100 C free air temperature at the rate of 2 mW/C.
 5. Denote linearly to 100 C free air temperature at the rate of 3.33 mW/C.



TIL113, TIL119A OPTOCOUPLERS

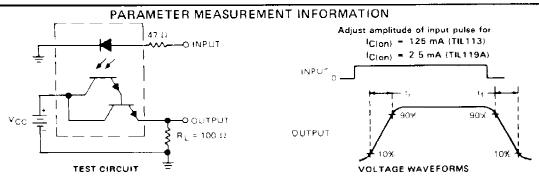
electrical characteristics at 25°C free-air temperature

PARAMETER		TEST CONDITIONS [†]			TIL113			TIL119A			UNIT	
					MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
V _(BR) CBO	Collector Base Breakdown Voltage	I _C = 10 μA.	ι _Ε - 0,	1F - 0	30						V	
V(BR)CEO	Collector-Emitter Breakdown Voltage	IC = 1 mA	+B = 0.	IF = 0	30			30			V	
V(BR)EBO	Emitter-Base Breakdown Voltage	IE = 10 μA,	I _C 0,	'F - 0	7				_		V	
V(BR)ECO	Emitter-Collector Breakdown Voltage	le = 10 μA.	lt = 0					7			V_	
1	On State	V _{CE} = 1 V.	1 _B = 0,	1 _F ≈ 10 mA	30	100		i			mA	
¹ C(un)	Collector Current	V _{CE} = 1 V.	I _F = 10 mA					30 160	160			
^I C(off)	Off-State Collector Current	V _{CE} = 10 V.	1 _B - 0,	1 _F - 0	i		100			100	nA	
μŁΕ	Transistor Static Forward Current Transfer Ratio	V _{CE} - 1 V,	I _Č - 10 mA.	le = 0		15,000						
v _F	Input Diode Static Forward Voltage	1p = 10 mA					1.5			1.5	V	
	Collector-Emitter	Ic = 125 mA,	l _B = 0,	l _F = 50 mA	Ī		1.2	1			J _v	
VCE (sat)	Saturation Voltage	¹ C = 30 mA.	lp = 10 mA					1			<u>l </u>	
110	Input-to-Output Internal Resistance	V _{in-out} = +1.5 kV	, See Note 6		1011			1011			Ω	
C _{IO}	Input-to-Output Capacitance	V _{in out} 10,	f= 1 MHz,	See Note 6		1	13	·	1	1.3	pΕ	

NOTE 6: These parameters are measured between both input-diode leads shorted together and all the phototransistor leads shorted together. Reference to the base are not applicable to TIL119A.

switching characteristics at 25 C free-air temperature

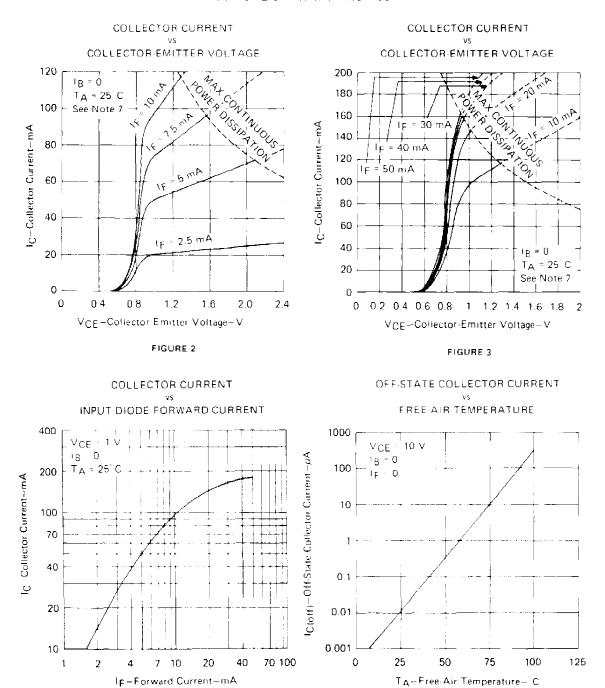
	DADAMETED.	TEST CONDITIONS		TL113			TIL119A		
1	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	TINU
1,	Rise Time	VCC - 15 V. IC(on) = 125 mA,		300					
1+	Fall Time	R _L = 100 Ω, See Figure 1		300					μS
1,	Rise Time	V _{CC} = 10 V, I _{C(on)} = 2.5 mA,					300		
1+	Fall Time	R _L - 100 Ω, See Figure 1					300		45



- NOTES: a The input waveform is supplied by a generator with the following characteristics: $Z_{out} = 50 \Omega_c t_r \approx 15 \text{ ns. duty cycle} \approx 1\%$.
 - t_W = 500 μs . b. The output waveform is monitored on an oscilloscope with the following characteristics: $t_n \lesssim 12$ ns, $R_{in} \approx 1$ M Ω , $C_{in} \lesssim 20$ pF

FIGURE 1-SWITCHING TIMES

TYPICAL CHARACTERISTICS



NOTE 7. Pulse operation of input diode is required for operation beyond limits shown by dotted line.

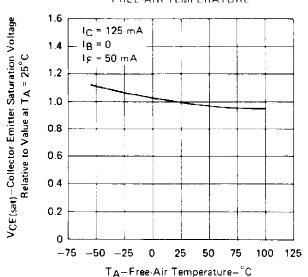
FIGURE 4



FIGURE 5

TYPICAL CHARACTERISTICS

RELATIVE COLLECTOR-EMITTER SATURATION VOLTAGE vs FREE-AIR TEMPERATURE



TIL113 TRANSISTOR STATIC FORWARD CURRENT TRANSFER RATIO vs COLLECTOR CURRENT

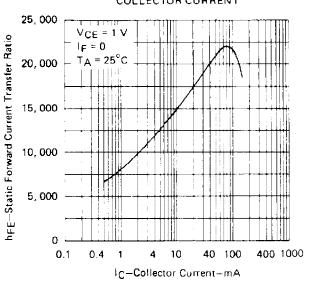
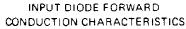
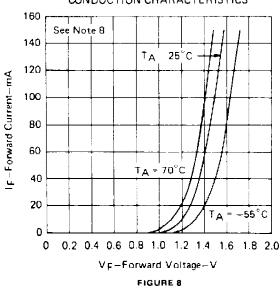


FIGURE 6

FIGURE 7





NOTE B: This parameter was measured using pulse techniques, $t_{\rm eff}$ = 1 ms, duty cycle \leq 2%.

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PACKAGE OPTION ADDENDUM

8-Apr-2005

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp (3)
TIL113	OBSOLETE	PDIP	N	6	TBD	Call TI	Call TI
TIL119	OBSOLETE	PDIP	N	6	TBD	Call TI	Call TI
TIL119A	OBSOLETE	PDIP	N	6	TBD	Call TI	Call TI

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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